

74HC1G00; 74HCT1G00

2-input NAND gate

Rev. 04 — 11 July 2007

Product data sheet

1. General description

The 74HC1G00 and 74HCT1G00 are high speed Si-gate CMOS devices. They provide a 2-input NAND function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC00 and 74HCT00.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options

3. Ordering information

Table 1. Ordering information

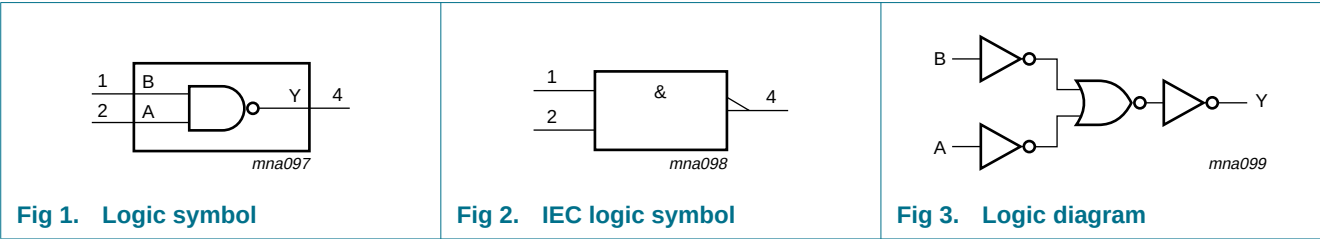
Type number	Package			
	Temperature range	Name	Description	Version
74HC1G00GW 74HCT1G00GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74HC1G00GV 74HCT1G00GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753

4. Marking

Table 2. Marking codes

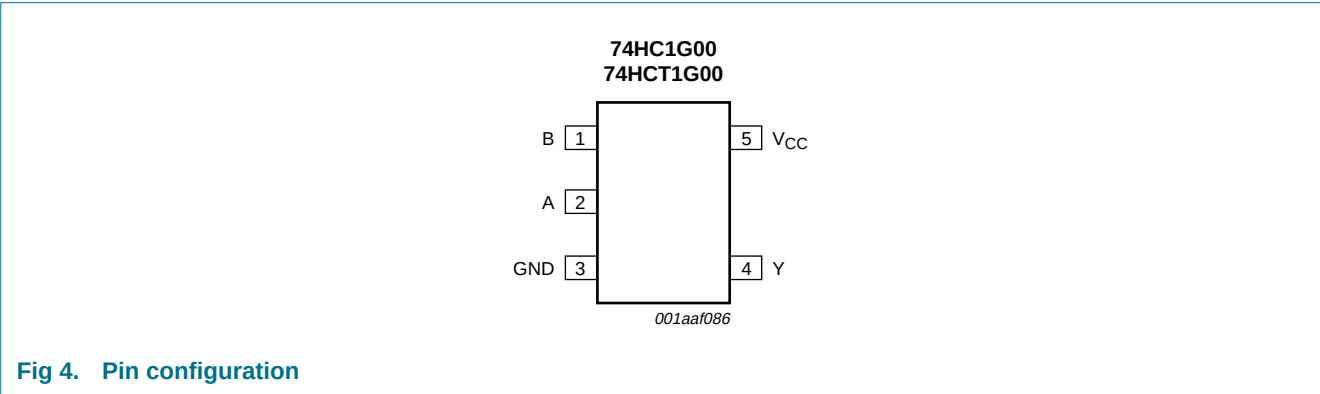
Type number	Marking
74HC1G00GW	HA
74HCT1G00GW	TA
74HC1G00GV	H00
74HCT1G00GV	T00

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
B	1	data input
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V _{CC}	5	supply voltage

7. Functional description

Table 4. Function table
H = HIGH voltage level; L = LOW voltage level

Input		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [\[1\]](#)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_O	output current	$-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$	-	± 12.5	mA
I_{CC}	supply current		-	25	mA
I_{GND}	ground current		-25	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C to }+125\text{ °C}$	[2] -	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1G00			74HCT1G00			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ °C}$.

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	

For type 74HC1G00

V_{IH}	HIGH-level input voltage	$V_{CC} = 2.0\text{ V}$	1.5	1.2	-	1.5	-	V
		$V_{CC} = 4.5\text{ V}$	3.15	2.4	-	3.15	-	V
		$V_{CC} = 6.0\text{ V}$	4.2	3.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 2.0\text{ V}$	-	0.8	0.5	-	0.5	V
		$V_{CC} = 4.5\text{ V}$	-	2.1	1.35	-	1.35	V
		$V_{CC} = 6.0\text{ V}$	-	2.8	1.8	-	1.8	V

Table 7. Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 2.0\text{ V}$	1.9	2.0	-	1.9	-	V
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	4.4	4.5	-	4.4	-	V
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 6.0\text{ V}$	5.9	6.0	-	5.9	-	V
		$I_O = -2.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	4.13	4.32	-	3.7	-	V
		$I_O = -2.6\text{ mA}$; $V_{CC} = 6.0\text{ V}$	5.63	5.81	-	5.2	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 2.0\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 6.0\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 2.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	0.15	0.33	-	0.4	V
		$I_O = 2.6\text{ mA}$; $V_{CC} = 6.0\text{ V}$	-	0.16	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0\text{ V}$	-	-	1.0	-	1.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$; $V_{CC} = 6.0\text{ V}$	-	-	10	-	20	μA
C_I	input capacitance		-	1.5	-	-	-	pF
For type 74HCT1G00								
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	2.0	1.6	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	1.2	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	4.4	4.5	-	4.4	-	V
		$I_O = -2.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	4.13	4.32	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 2.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	0.15	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5\text{ V}$	-	-	1.0	-	1.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$; $V_{CC} = 5.5\text{ V}$	-	-	10	-	20	μA
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5\text{ V to }5.5\text{ V}$; $V_I = V_{CC} - 2.1\text{ V}$; $I_O = 0\text{ A}$	-	-	500	-	850	μA
C_I	input capacitance		-	1.5	-	-	-	pF

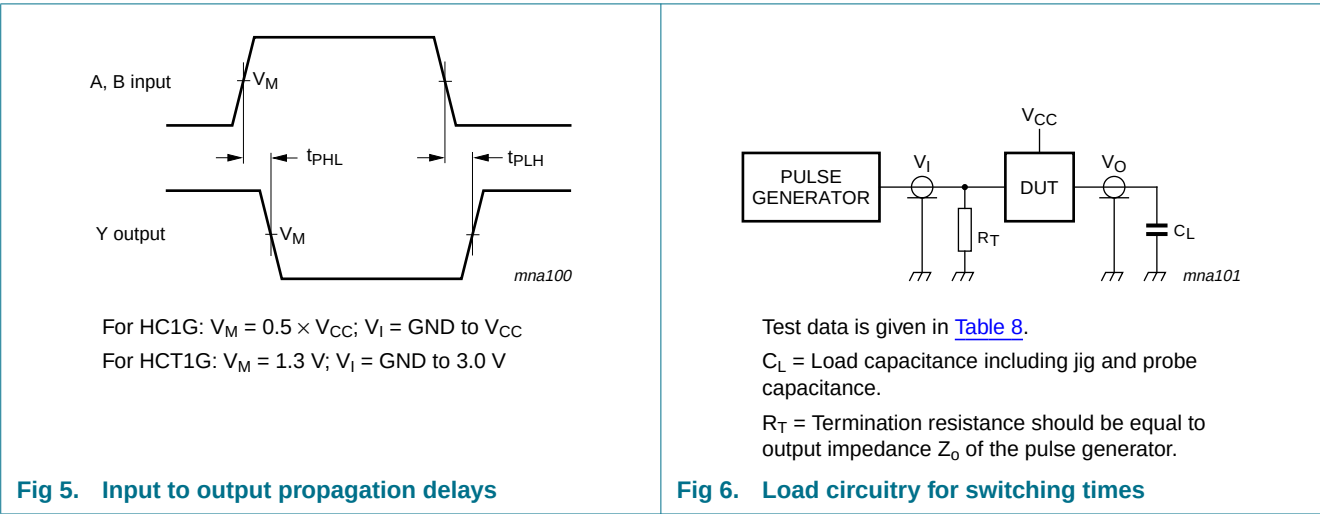
11. Dynamic characteristics

Table 8. Dynamic characteristics
GND = 0 V; $t_r = t_f \leq 6.0\text{ ns}$; All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$. For test circuit see [Figure 6](#)

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
For type 74HC1G00								
t _{pd}	propagation delay	A and B to Y; see Figure 5	[1]					
		V _{CC} = 2.0 V; C _L = 50 pF	-	25	115	-	135	ns
		V _{CC} = 4.5 V; C _L = 50 pF	-	9	23	-	27	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	7	-	-	-	ns
		V _{CC} = 6.0 V; C _L = 50 pF	-	8	20	-	23	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC}	[2]	-	19	-	-	pF
For type 74HCT1G00								
t _{pd}	propagation delay	A and B to Y; see Figure 5	[1]					
		V _{CC} = 4.5 V; C _L = 50 pF	-	12	24	-	27	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	10	-	-	-	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} – 1.5 V	[2]	-	21	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [2] C_{PD} is used to determine the dynamic power dissipation P_D (μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz; f_o = output frequency in MHz
 C_L = output load capacitance in pF
 V_{CC} = supply voltage in Volts
 $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs

12. Waveforms



13. Package outline

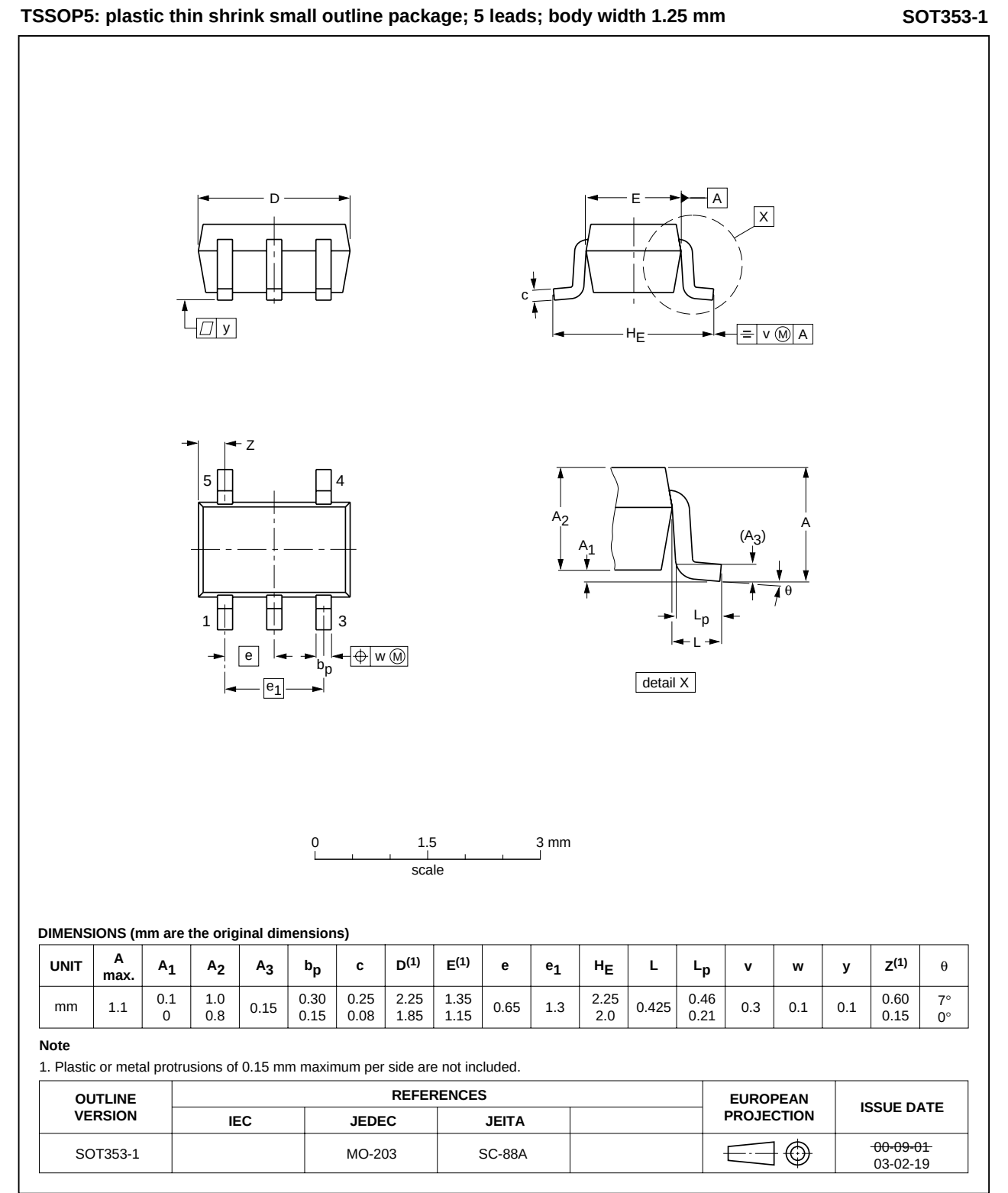


Fig 7. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

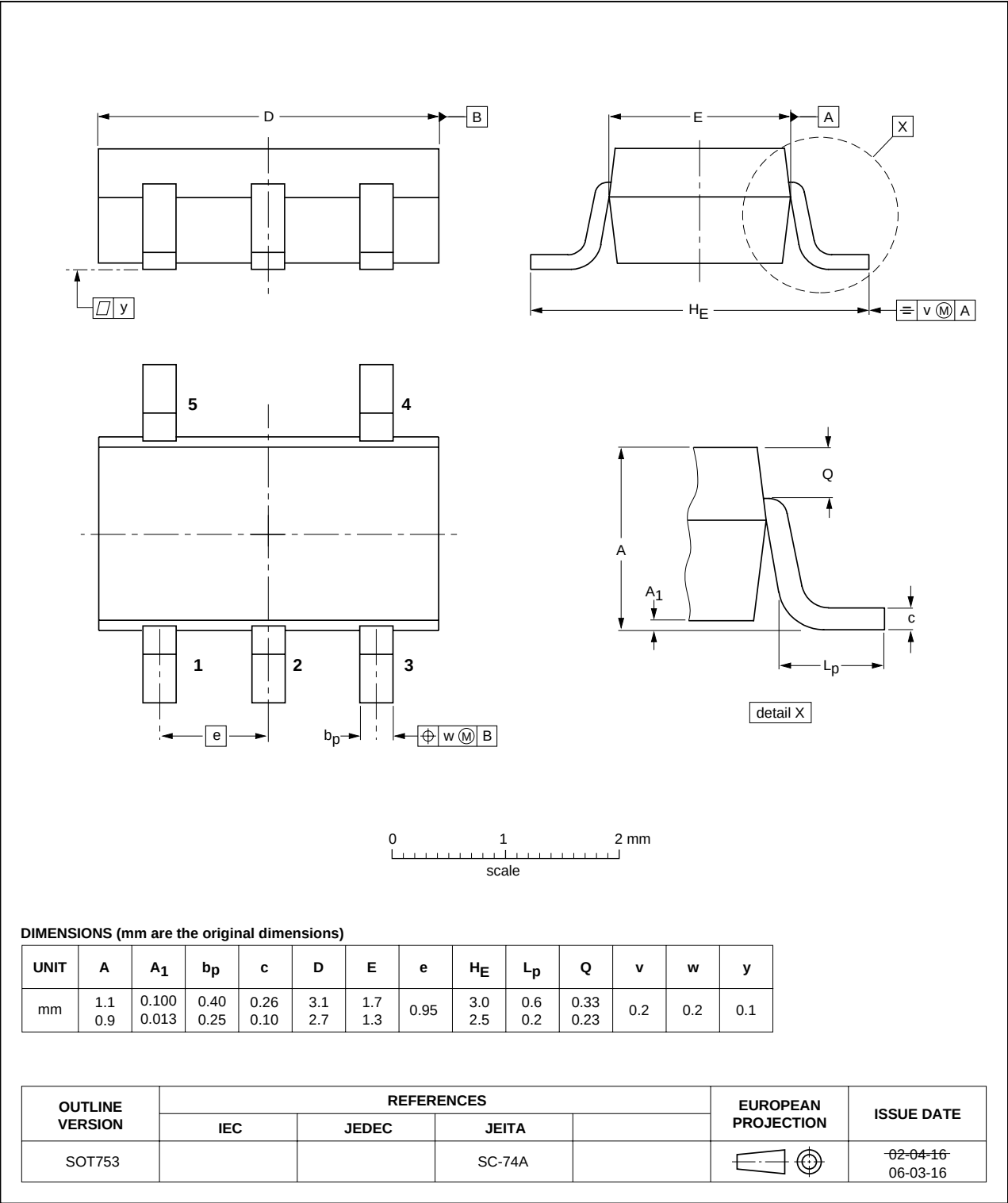


Fig 8. Package outline SOT753 (SC-74A)

14. Abbreviations

Table 9. Abbreviations

Acronym	Description
DUT	Device Under Test
TTL	Transistor-Transistor Logic

15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G00_4	20070711	Product data sheet	-	74HC_HCT1G00_3
Modifications:	- The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. - Legal texts have been adapted to the new company name where appropriate. - Package SOT353 changed to SOT353-1 in Section 3 and Section 13. - Quick reference data and Soldering sections removed. Section 2 "Features" updated.			
74HC_HCT1G00_3	20020515	Product specification	-	74HC_HCT1G00_2
74HC_HCT1G00_2	20010302	Product specification	-	74HC_HCT1G00_1
74HC_HCT1G00_1	19980730	Preliminary specification	-	-

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16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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